

# MGFC39V5258

## 5.2~5.8GHz BAND 8W INTERNALLY MATCHED GaAs FET

### DESCRIPTION

The MGFC39V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 ~ 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

### FEATURES

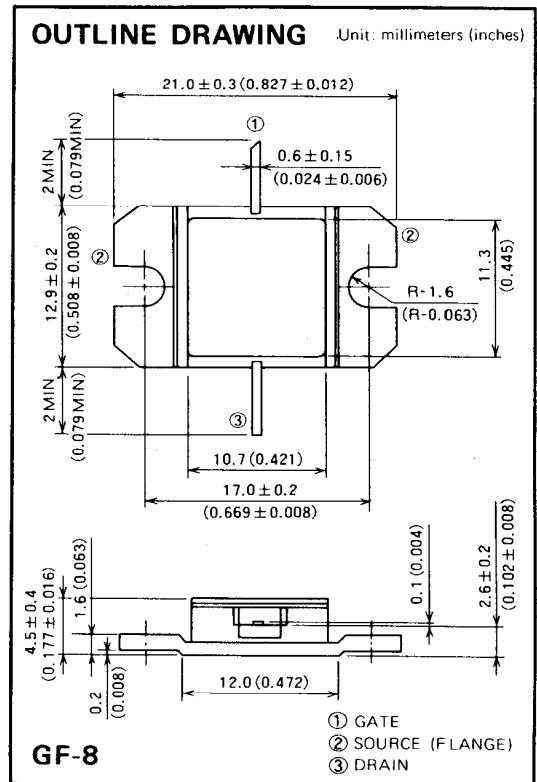
- Class A operation
- Internally matched to 50Ω system
- High output power  
 $P_{1dB} = 8 \text{ W (TYP) @ 5.2 ~ 5.8 GHz}$
- High power gain  
 $G_{LP} = 9 \text{ dB (TYP) @ 5.2 ~ 5.8 GHz}$
- High power added efficiency  
 $\eta_{add} = 30\% \text{ (TYP) @ 5.2 ~ 5.8 GHz, } P_{1dB}$
- Hermetically sealed metal-ceramic package

### APPLICATION

5.2 ~ 5.8 GHz band power amplifiers.

### QUALITY GRADE

- IG



### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| Symbol           | Parameter                   | Ratings    | Unit |
|------------------|-----------------------------|------------|------|
| V <sub>GDO</sub> | Gate to drain voltage       | -15        | V    |
| V <sub>GSO</sub> | Gate to source voltage      | -15        | V    |
| I <sub>D</sub>   | Drain current               | 5.6        | A    |
| I <sub>GR</sub>  | Reverse gate current        | -20        | mA   |
| I <sub>GF</sub>  | Forward gate current        | +42        | mA   |
| P <sub>T</sub>   | Total power dissipation * 1 | 42.8       | W    |
| T <sub>ch</sub>  | Channel temperature         | 175        | °C   |
| T <sub>stg</sub> | Storage temperature         | -65 ~ +175 | °C   |

\* 1: T<sub>C</sub> = 25°C

### RECOMMENDED BIAS CONDITIONS

- V<sub>DS</sub> = 10V
- I<sub>D</sub> = 2.4A
- R<sub>g</sub> = 50Ω
- Refer to Bias Procedure

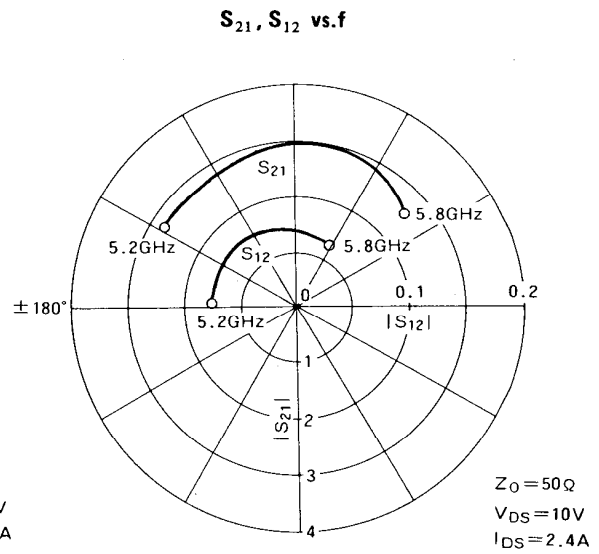
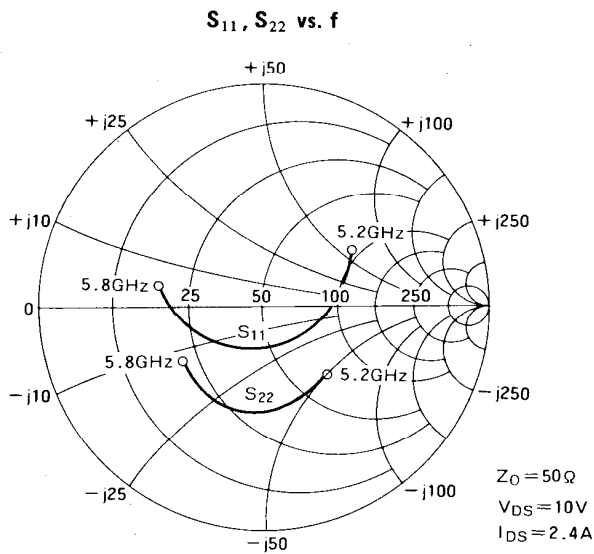
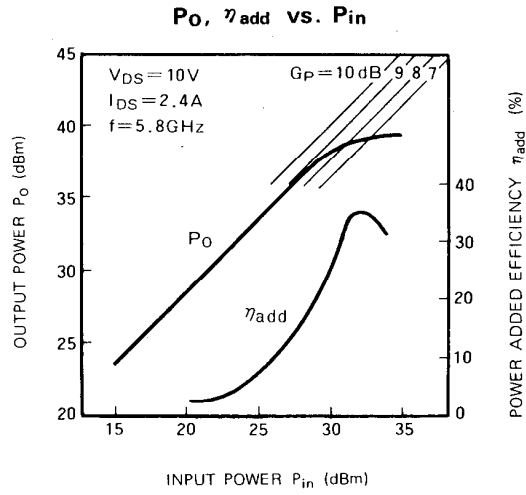
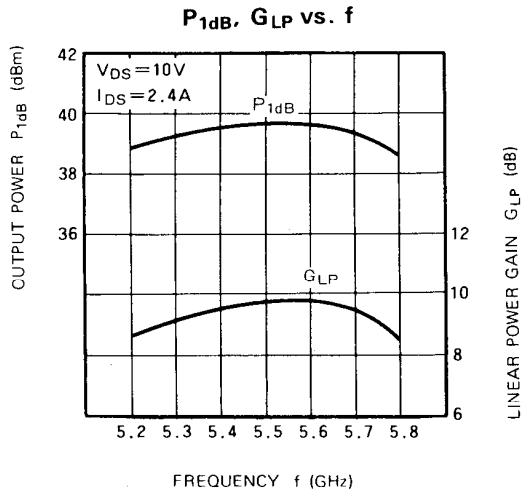
### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| Symbol                | Parameter                            | Test conditions  | Limits                 |     |     | Unit |
|-----------------------|--------------------------------------|--|------------------------|-----|-----|------|
|                       |                                      |  | Min                    | Typ | Max |      |
| I <sub>DSS</sub>      | Saturated drain current              | V <sub>DS</sub> = 3V, V <sub>GS</sub> = 0V                     | —                      | 4.0 | 5.6 | A    |
| g <sub>m</sub>        | Transconductance                     | V <sub>DS</sub> = 3V, I <sub>D</sub> = 2.2A                    | —                      | 2.0 | —   | S    |
| V <sub>GS(off)</sub>  | Gate to source cut-off voltage       | V <sub>DS</sub> = 3V, I <sub>D</sub> = 20mA                    | -2                     | -3  | -4  | V    |
| P <sub>1dB</sub>      | Output power at 1dB gain compression | V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.4A, f = 5.2 ~ 5.8GHz | 38                     | 39  | —   | dBm  |
| G <sub>LP</sub>       | Linear power gain                    |  | 8                      | 9   | —   | dB   |
| I <sub>D</sub>        | Drain current                        |  | —                      | 2.2 | 1.4 | A    |
| η <sub>add</sub>      | Power added efficiency               |  | —                      | 30  | —   | %    |
| R <sub>th(ch-c)</sub> | Thermal resistance * 1               |  | ΔV <sub>f</sub> method | —   | —   | 3.5  |

\* 1: Channel to case

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**TYPICAL CHARACTERISTICS** ( $T_a=25^\circ\text{C}$ )



**S PARAMETERS** ( $T_a=25^\circ\text{C}$ ,  $V_{DS}=10\text{V}$ ,  $I_{DS}=2.4\text{A}$ )

| f<br>(GHz) | S Parameters (TYP.) |              |          |              |          |              |          |              |
|------------|---------------------|--------------|----------|--------------|----------|--------------|----------|--------------|
|            | $S_{11}$            |              | $S_{21}$ |              | $S_{12}$ |              | $S_{22}$ |              |
|            | Magn.               | Angle (deg.) | Magn.    | Angle (deg.) | Magn.    | Angle (deg.) | Magn.    | Angle (deg.) |
| 5.2        | 0.48                | 32           | 2.69     | 148          | 0.076    | 178          | 0.42     | -47          |
| 5.3        | 0.36                | 11           | 2.80     | 133          | 0.077    | 164          | 0.43     | -61          |
| 5.4        | 0.26                | -19          | 2.79     | 114          | 0.077    | 146          | 0.45     | -77          |
| 5.5        | 0.19                | -71          | 2.99     | 99           | 0.076    | 127          | 0.47     | -95          |
| 5.6        | 0.26                | -139         | 2.98     | 81           | 0.070    | 105          | 0.48     | -113         |
| 5.7        | 0.38                | -170         | 2.95     | 62           | 0.068    | 84           | 0.46     | -130         |
| 5.8        | 0.49                | 169          | 2.70     | 41           | 0.065    | 61           | 0.45     | -146         |

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